



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Huang

Serial No.: 09/270,039

Confirmation No.: 0424

Filed: March 16, 1999

For: IN SITU DEPOSITION OF A LOW K
DIELECTRIC LAYER, BARRIER
LAYER, ETCH STOP, AND ANTI-
REFLECTIVE COATING FOR
DAMASCENE APPLICATION

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

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§ Group Art Unit: 2823
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§ Examiner: G. Fourson
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I hereby certify that this correspondence is being deposited on <u>September 21, 2001</u> with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231	
<u>9/21/01</u> Date	<u>[Signature]</u> Signature

RESPONSE TO OFFICE ACTION DATED JUNE 21, 2001

In response to the Office Action dated June 21, 2001, having a shortened statutory period for response set to expire on September 21, 2001, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

IN THE CLAIMS:

Please cancel claims 1-13 without prejudice, and amend the following claims:

1. (Cancelled) A substrate, comprising:
a silicon carbide layer having a dielectric constant less than 7.0 and deposited on the substrate;
a first dielectric layer deposited on the silicon carbide layer *in situ* with the silicon carbide layer; and